

## N-Channel Enhancement Mode Power MOSFET

## **DESCRIPTION**

The PT 3400Ó uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **GENERAL FEATURES**

•  $V_{DS} = 30V, I_D = 5.8A$ 

 $R_{DS(ON)}$  < 59m $\Omega$  @  $V_{GS}$ =2.5V

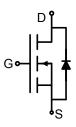
 $R_{DS(ON)} < 45 \text{m}\Omega$  @  $V_{GS}$ =4.5V

 $R_{DS(ON)}$  < 41m $\Omega$  @  $V_{GS}$ =10V

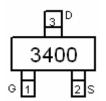
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

## **Application**

- PWM applications
- Load switch
- ●Power management



Schematic diagram



Marking and pin Assignment



SOT-23 top view

## **Package Marking And Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3400 / <del>//////////////////////////////////</del>	<b>₩₩</b> ₽Т 3400Ó	SOT-23	Ø180mm	8 mm	3000 units

# Absolute Maximum Ratings (TA=25℃unless otherwise noted)

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Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Drain Current-Continuous	I <sub>D</sub>	5.8	А
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	30	А
Maximum Power Dissipation	P <sub>D</sub>	1.4	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	1.0	°C/W
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#### Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition		Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	33	-	V

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Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.7	0.9	1.4	V
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4A	-	45	59	mΩ
ain-Source On-State Resistance	$R_{DS(ON)}$	V <sub>GS</sub> =4.5V, I <sub>D</sub> =2.9A	-	34	45	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =2.9A	-	31	41	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =2.9A	10	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C <sub>lss</sub>	\/ -15\/\/ -0\/	-	623	-	PF
Output Capacitance	Coss	$V_{DS}$ =15V, $V_{GS}$ =0V, F=1.0MHz	-	99	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0IVID2	-	77	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	3.3	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =15V,I <sub>D</sub> =2.9A	-	4.8	-	nS
Turn-Off Delay Time	$t_{\sf d(off)}$	$V_{GS}$ =10V, $R_{GEN}$ =3 $\Omega$	-	26	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Qg	V 45VI 5.0A	-	9.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A,	-	1.5	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V	-	3	-	nC
Drain-Source Diode Characteristics	1	<u>'</u>	· ·			ı
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =2.9A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	2.9	Α
		1		1		

## Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

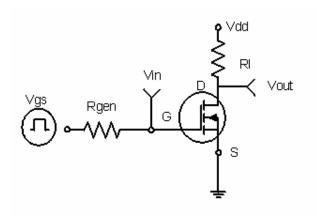


Figure 1: Switching Test Circuit

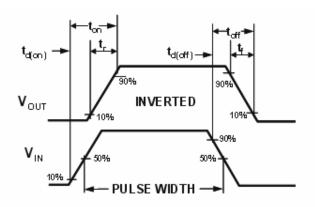
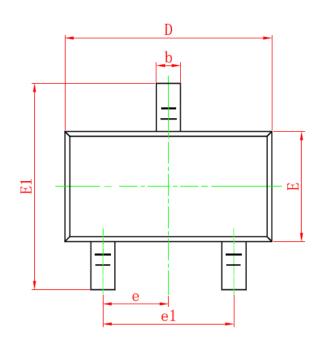
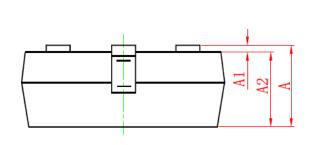
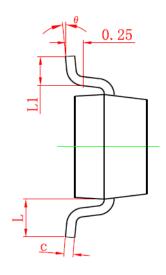


Figure 2:Switching Waveforms

# **SOT-23 PACKAGE INFORMATION**







Cumbal	Dimensions in Millimeters			
Symbol	MIN.	MAX.		
Α	0.900	1.150		
A1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
E	1.200	1.400		
E1	2.250	2.550		
е	0.950TYP			
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0°	8°		

#### **NOTES**

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$

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